UMW IRF9Z34N

-55V P-Channel MOSFET

1.Description

The TO-220 package is universally preferred for all commercial-industrial applications at power dissipation levels to approximately 50 watts.

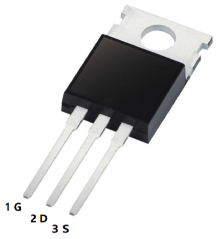
2.Features

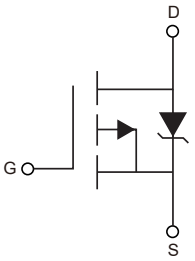
- $V_{DS\ (V)}$=-55V
- I_D=-19A
- $R_{DS(ON)}$<100mΩ(V_{GS}=-10V)

3.Pinning information

Pin	Symbol	Description
1	G	GATE
2	D	DRAIN
3	S	SOURCE

TO-220





4.Absolute Maximum Ratings

Parameter		Symbol	Rating	Units
Continuous Drain Current, V_{GS}=-10V	T_C=25°C	I_D	-19	A
Continuous Drain Current, V_{GS}=-10V	T_C=100°C		-14	A
Pulsed Drain Current ①		I_{DM}	-68	A
Power Dissipation	T_C=25°C	P_D	68	W
Linear Derating Factor			0.45	W/°C
Gate-to-Source Voltage		V_{GS}	±20	V
Single Pulse Avalanche Energy②		E_{AS}	180	mJ
Avalanche Current①		I_{AR}	-10	A
Repetitive Avalanche Energy①		E_{AR}	6.8	mJ
Peak Diode Recovery dv/dt ③		dv/dt	-5	V/ns
Storage Temperature Range		T_J, T_{STG}	-55 to 175	°C
Soldering Temperature, for 10 seconds			300 (1.6mm from case)	°C
Mounting torque, 6-32 or M3 screw			10 lbf•in (1.1N•m)	

5.Thermal resistance rating

Parameter	Symbol	Typ	Max	Units
Junction-to-Case	$R_{\theta JC}$		2.2	°C/W
Case-to-Sink, Flat, Greased Surface	$R_{\theta CS}$	0.5		°C/W
Junction-to-Ambient	$R_{\theta JA}$		62	°C/W

6.Electrical Characteristics @ T_J= 25°C (unless otherwise specified)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	I_D=-250μA, V_{GS}=0V	-55			V
Breakdown Voltage Temp. Coefficient	$\Delta V_{(BR)DSS}/T_J$	I_D=-1mA,Reference to 25°C		-0.05		V/°C
Static Drain-to-Source On-Resistance	$R_{DS(ON)}$	V_{GS}=-10V, I_D=-10A ④			100	mΩ
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=-250μA	-2		-4	V
Forward Transconductance	g_{FS}	V_{DS}=25V, I_D=-10A	4.2			S
Drain-to-Source Leakage Current	I_{DSS}	V_{DS}=-55V, V_{GS}=0V			-25	μA
		V_{DS}=-44V,V_{GS}=0V,T_J=150°C			-250	μA
Gate-to-Source Forward Leakage	I_{GSS}	V_{GS}=20V			100	nA
Gate-to-Source Reverse Leakage		V_{GS}=-20V			-100	nA
Total Gate Charge	Q_g	I_D=-10A			35	nC
Gate-to-Source Charge	Q_{gs}	V_{DS}=-44V, V_{GS}=-10V			7.9	nC
Gate-to-Drain ("Miller") Charge	Q_{gd}	See Fig. 6 and 13 ④			16	nC
Turn-On Delay Time	$t_{D(on)}$	V_{DD}=-28V, I_D=-10A R_G=13Ω, R_D=2.6Ω See Fig. 10 ④		13		ns
Rise Time	t_r			55		ns
Turn-Off Delay Time	$t_{D(off)}$			30		ns
Fall Time	t_f			41		ns
Internal Drain inductance	L_D	Between lead, 6mm (0.25in.) from package and center of die contact		4.5		nH
Internal Source inductance	L_S			7.5		nH
Input Capacitance	C_{iss}	V_{GS}=0V, V_{DS}=-25V f=1.0MHz, See Fig. 5		620		pF
Output Capacitance	C_{oss}			280		pF
Reverse Transfer Capacitance	C_{rss}			140		pF

Source-Drain Ratings and Characteristics						
Continuous Source Current (Body Diode)	I_S	MOSFET symbol showing the integral reverse p-n junction diode.			-19	A
Pulsed Source Current (Body Diode) ①	I_{SM}				-68	A
Diode Forward Voltage	V_{SD}	T_J=25°C, I_S=-10A, V_{GS}=0V ④			-1.6	V
Reverse Recovery Time	t_{rr}	T_J=25°C, I_F=-10A dI/dt=-100A/μs ④		54	82	ns
Reverse Recovery Charge	Q_{rr}			110	160	nC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S+L_D)				

Notes:

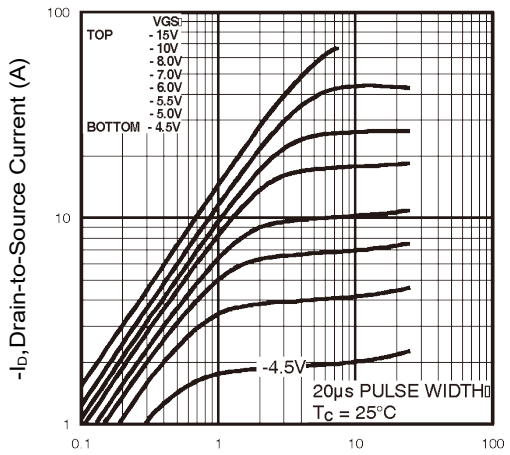
① Repetitive rating; pulse width limited by max. junction temperature.

② Starting T_J= 25°C,L= 3.6mH, R_G=25Ω,I_{AS}=-10A.

③ I_{SD} ≤-10A, di/dt ≤ -290A/μs, V_{DD} ≤ $V_{(BR)DSS}$,T_J ≤ 175°C.

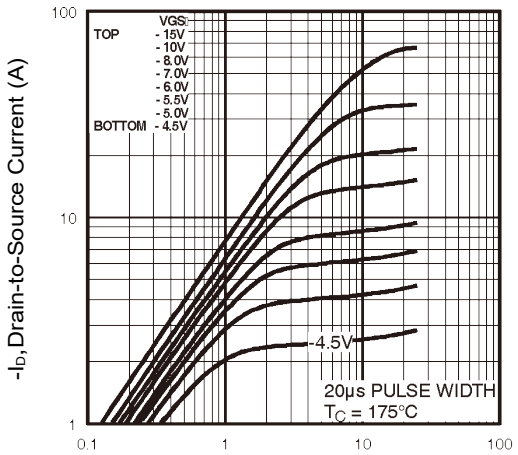
④ Pulse width ≤ 300μs; duty cycle ≤ 2%.

7.1Typical Characterisitics



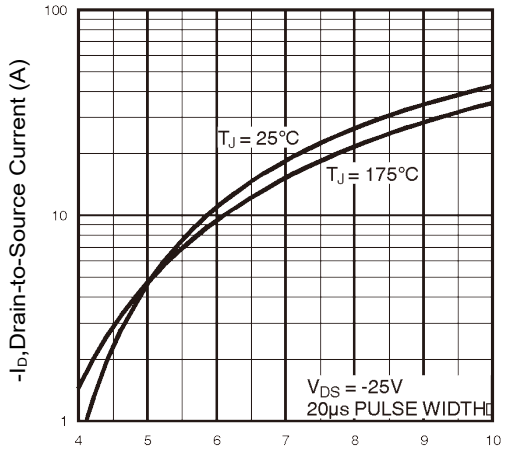
-V_{DS},Drain-to-Source Voltage (V)

Figure 1: Typical Output Characteristics



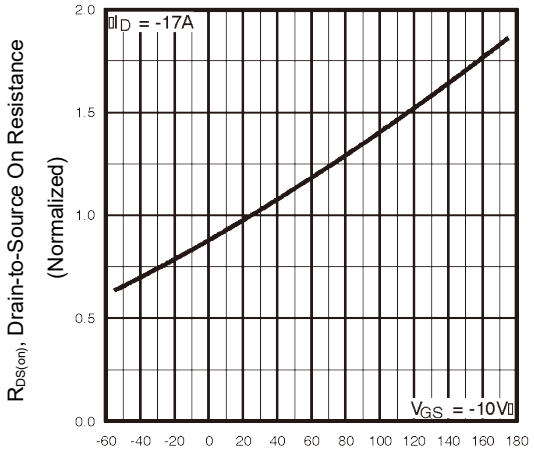
-V_{DS},Drain-to-Source Voltage (V)

Figure 2: Typical Output Characteristics



-V_{GS}, Gate-to-Source Voltage (V)

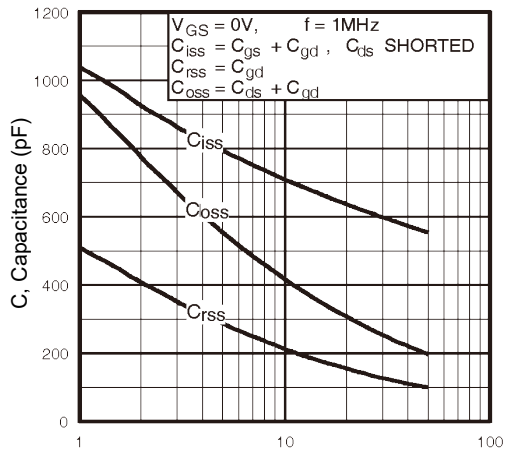
Figure 3: Typical Transfer Characteristics



T_J, Junction Temperature (°C)

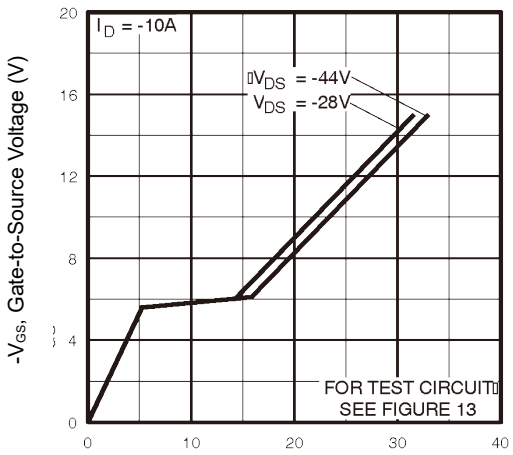
Figure 4: Nomalized On-ResistanceVs. Temperature

7.2Typical Characterisitics



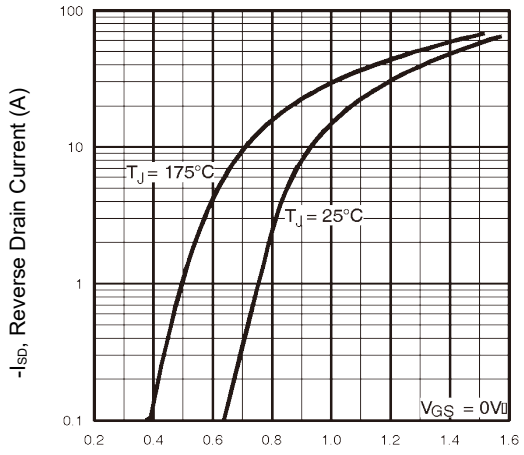
-V_{DS} ,Drain-to-Source Voltage (V)

Figure 5: Typical Capacitance Vs. Drain-to-Source Voltage



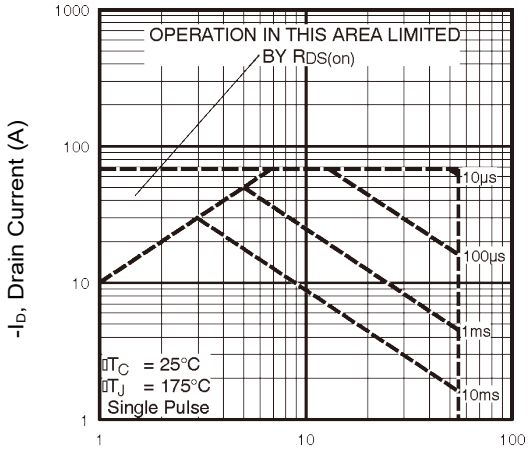
Q_G, Total Gate Charge (nC)

Figure 6: Typical Gate Charge Vs. Gate-to-Source Voltage



-V_{SD}, Source-to-Drain Voltage (V)

Figure 7: Typical Source-Drain Diode Forward Voltage



-V_{DS}, Drain-to-Source Voltage (V)

Figure 8: Maximum Safe Operating Area

7.3Typical Characterisitics

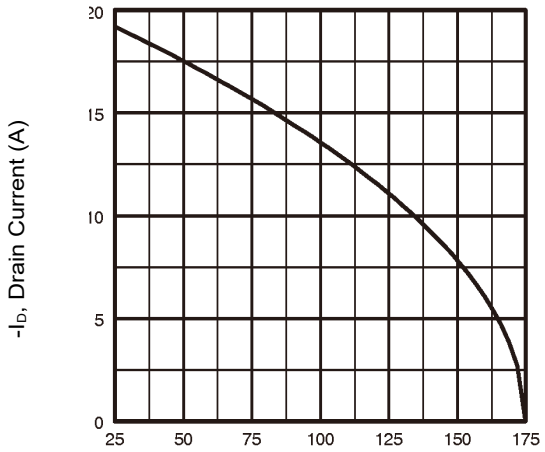


Figure 9: Maximum Drain Current Vs.
Case Temperature

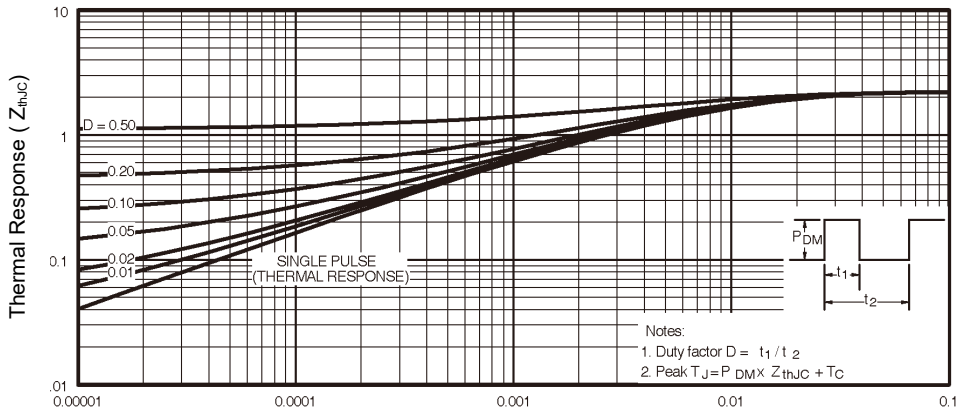


Figure 11: Maximum Effective Transient Thermal Impedance, Junction-to-Case

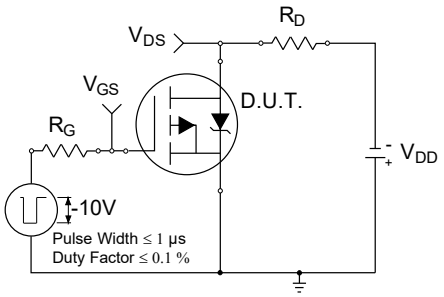


Figure 12a: Switching Time Test Circuit

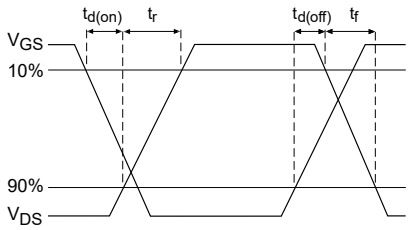


Figure 12b: Switching Time Waveforms

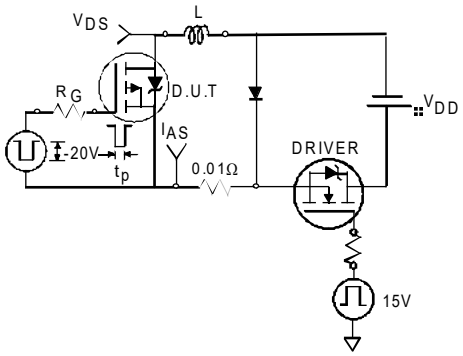


Figure 13a: Unclamped Inductive Test Circuit

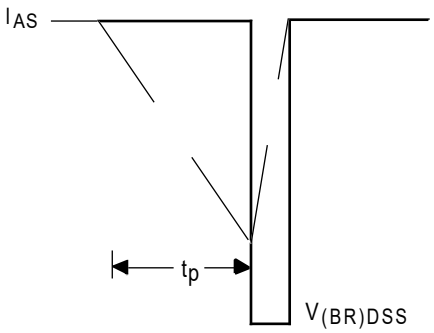


Figure 13b: Unclamped Inductive Waveforms

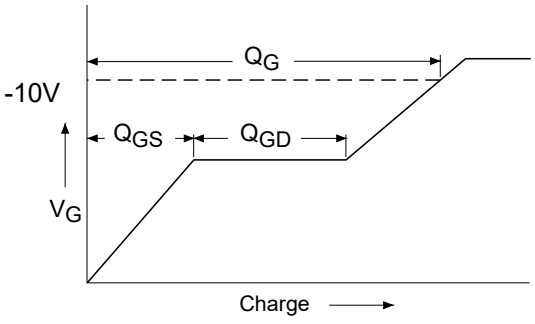


Figure 14a: Basic Gate Charge Waveform

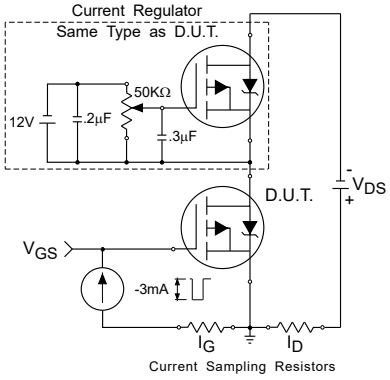
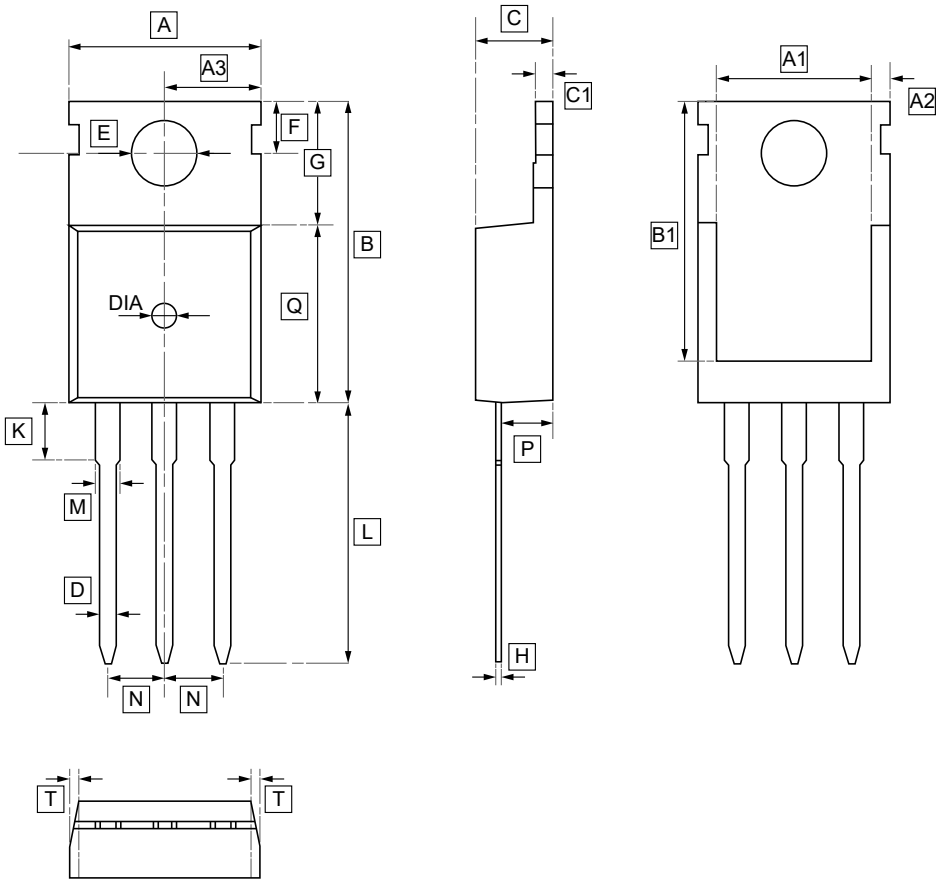


Figure 14b: Gate Charge Test Circuit

8.1 TO-220 Package Outline Dimensions

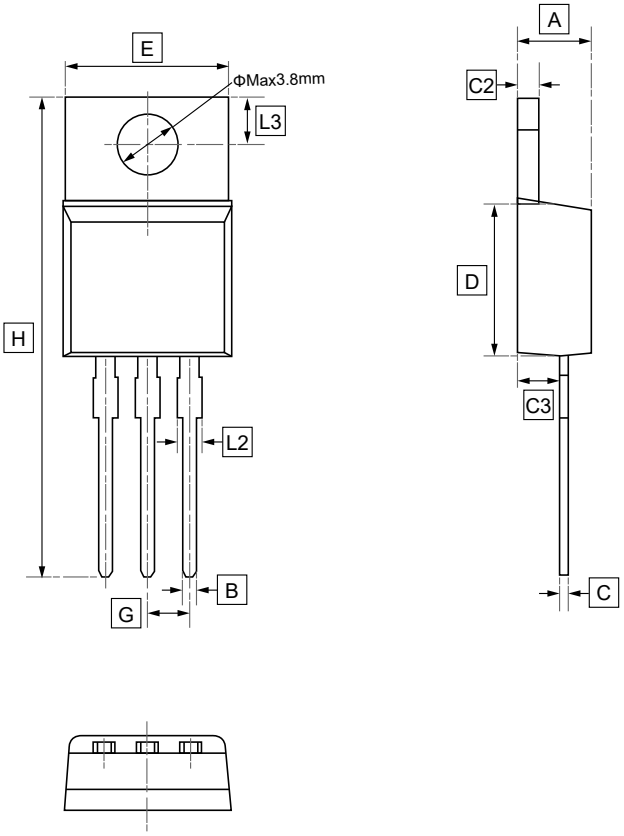


DIMENSIONS (mm are the original dimensions)

Symbol	A	A1	A2	A3	B	B1	C	C1	D	E	F	G
Min	9.7	8.44	1.05	4.8	15.4	12.9	4.28	1.1	0.6	3.4	2.65	5.2
Max	10.3	8.84	1.25	5.2	16.2	13.5	4.68	1.5	1.0	3.8	3.25	5.8

Symbol	H	K	L	L1	M	N	P	Q	T	DIA
Min	0.4	2.9	12.8	2.7	1.15	2.49	2.1	8.7	W:0.35	⊙1.5
Max	0.6	3.3	13.6	3.3	1.35	2.59	2.7	9.3		(deep 0.2)

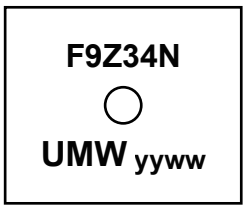
8.2 TO-220 Package Outline Dimensions



DIMENSIONS (mm are the original dimensions)

Symbol	A	B	C	C2	C3	D	E	G	H	L2	L3
Min	4.30	0.60	0.28	1.17	2.30	8.80	9.80	2.44	28.55	1.10	2.59
Max	4.70	1.00	0.48	1.37	2.70	9.20	10.20	2.64	29.15	1.50	2.89

9.Ordering information



yy: Year Code
ww: Week Code

Order Code	Package	Base QTY	Delivery Mode
UMW IRF9Z34N	TO-220	1000	Tube and box

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